



The DNA of tech.®

TSHF5211 890 nm IR Emitting Diode Offers
High Typical Radiant Intensity

High Speed Device Features Excellent Temperature Coefficient and Fast Switching Times

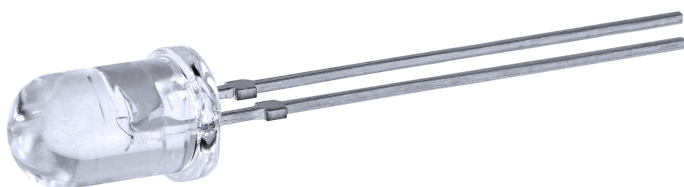


ADVANTAGE

Built on surface emitter technology,
device has 50 % higher radiant
intensity than previous generation

KEY PRODUCT FEATURES

- ✓ Excellent -1.0 mV/K temperature coefficient of V_F
- ✓ High typical radiant intensity of 235 mW/sr at a 100 mA drive current
- ✓ Fast switching times of 15 ns and low typ. forward voltage of 1.5 V
- ✓ Clear, untinted 5 mm leaded plastic package
- ✓ Narrow $\pm 10^\circ$ angle of half intensity



MARKETS AND APPLICATIONS



CONSUMER

- Entertainment
- Appliances



INDUSTRIAL

- Automation

ADDITIONAL BENEFITS

- Offers good spectral matching with silicon photodetectors
- RoHS-compliant, halogen-free, and Vishay Green
- Lead (Pb)-free and capable of lead (Pb)-free soldering up to 260 °C

RESOURCES



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